Product data sheet

1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

3. Applications

- · DC to DC converters
- Freewheeling diode
- · OR-ing diode
- · Switched mode power supply rectifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		100				V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 135 °C; per diode; Fig. 1; Fig. 2; Fig. 3		15			
$I_{O(AV)}$	average output current	δ = 0.5 ; square-wave pulse; $T_{mb} \le$ 134 °C; both diodes conducting	30				А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	$I_F = 5 \text{ A}$; $T_j = 25 ^{\circ}\text{C}$; per diode; Fig. 6		-	0.51	-	V
		I _F = 5 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.46	-	V
		I _F = 15 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.7	0.77	V
		I _F = 15 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.64	0.67	V
I _R	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8		-	-	50	μA
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8		-	-	30	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1 A2
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		ojiii 20

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S30100C	TO220	WN3S30100CQ	Tube	50	SOT78	13-Jun-2008

7. Marking

Table 4. Marking codes

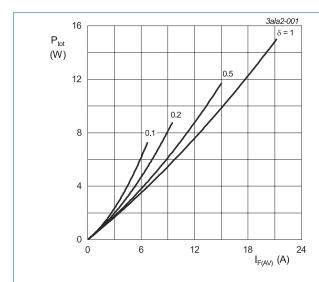
Type number	Marking codes
WN3S30100C	WN3S 30100C

8. Limiting values

Table 5. Limiting values

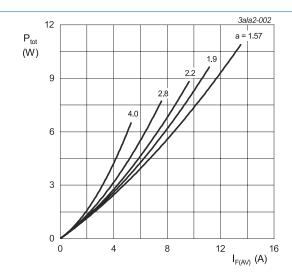
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		100	V
V_{RWM}	crest working reverse voltage		100	V
V_R	reverse voltage	DC	100	V
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 135$ °C; per diode; Fig. 1; Fig. 2; Fig. 3	15	А
$I_{O(AV)}$	average output current	δ = 0.5 ; square-wave pulse; $T_{mb} \le 134$ °C; both diodes conducting	30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	300	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	330	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 0.534 \text{ V; R}_s = 0.0082 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 0.534 V; R_s = 0.0082 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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Dual power Schottky diode

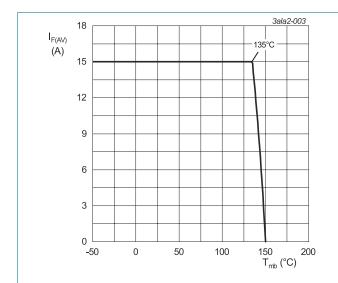


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

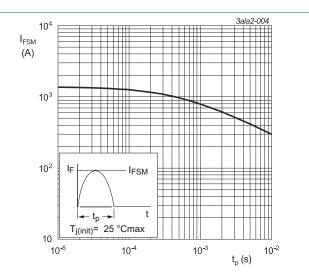


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance		per diode; <u>Fig. 5</u>	-	-	1.3	K/W
	from junction to mounting base	both diodes conducting	-	-	0.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

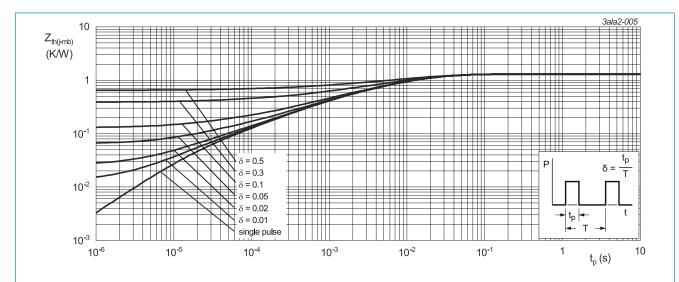
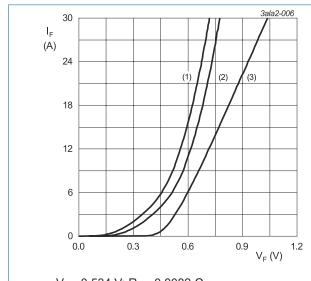


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F forward voltage		I _F = 5 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	0.51	-	V
		I _F = 5 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.46	-	V
		I _F = 15 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	0.7	0.77	V
		I _F = 15 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.64	0.67	V
I _R	reverse current	$V_R = 100 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	50	μΑ
		V _R = 100 V; T _j = 125 °C; per diode; Fig. 7; Fig. 8	-	-	30	mA



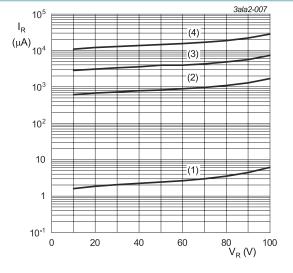
 $V_o = 0.534 \text{ V}; R_s = 0.0082 \Omega$

(1) $T_j = 150 \, ^{\circ}\text{C}$; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



(1) T_i = 25 °C; typical values

(2) T_j = 100 °C; typical values

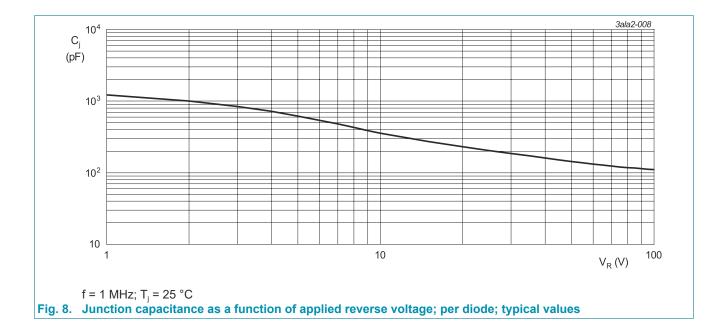
(3) $T_j = 125$ °C; typical values

(4) T_i = 150 °C; typical values

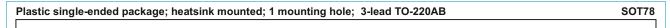
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

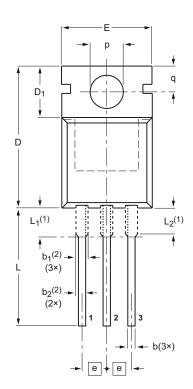
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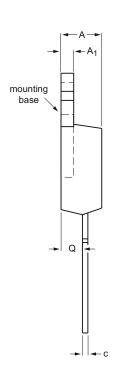
Dual power Schottky diode



11. Package outline







0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE	OUTLINE REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10	. Characteristics	6
11	. Package outline	8
12	Legal information	9
13	. Contents	11

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